

REMARKS/ARGUMENTS

The present invention aims to provide a dielectric device and a semiconductor device capable of forming sophisticated electronic components and transistors on a glass substrate or a plastic substrate.

When it is enabled to form an electronic device on a glass substrate or a plastic substrate, it becomes possible to form an integrated circuit directly on everything and to produce a flat panel display, such as a sophisticated liquid crystal display and EL display. However, since a glass substrate or a plastic substrate starts to be distorted at a low temperature, a process at a temperature of 600°C or over cannot be carried out. On the other hand, when a dielectric film was formed at a process temperature of 600°C or less, it had numerous defects in crystalline structure, so that a fine quality dielectric film could not be obtained. The present invention aims to clear such a problem.

According to the present invention, a fine quality dielectric film with very few defects in crystalline structure can be formed, even if a dielectric deposition process is carried out at 600°C or less. On the other hand, according to the invention of cited US 6,613,695 B2, a single crystal silicon substrate is used, so that the dielectric deposition process can be carried out at 1000°C or over, and a high quality dielectric deposition can be formed thereby. The cited reference (US 6,613,695 B2) does not at all disclose an art to enable to form a fine quality dielectric deposition with very few defects in crystalline structure by a process at a low temperature of 600°C or less.

Respectfully submitted,
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